

Dual Threshold X-Ray Photon Counter

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Dual Threshold X-Ray Photon Counter (DT-XPC)

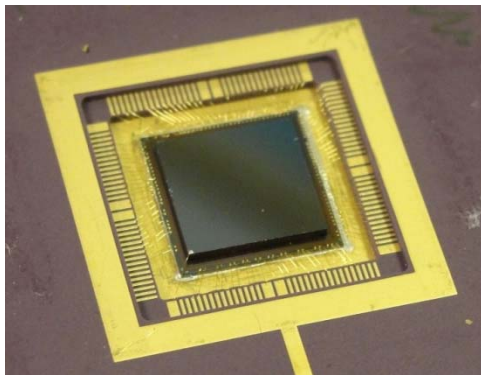
Advanced Photon Source (APS)



24-bunch mode: 80ps (FWHM) 153ns spacing



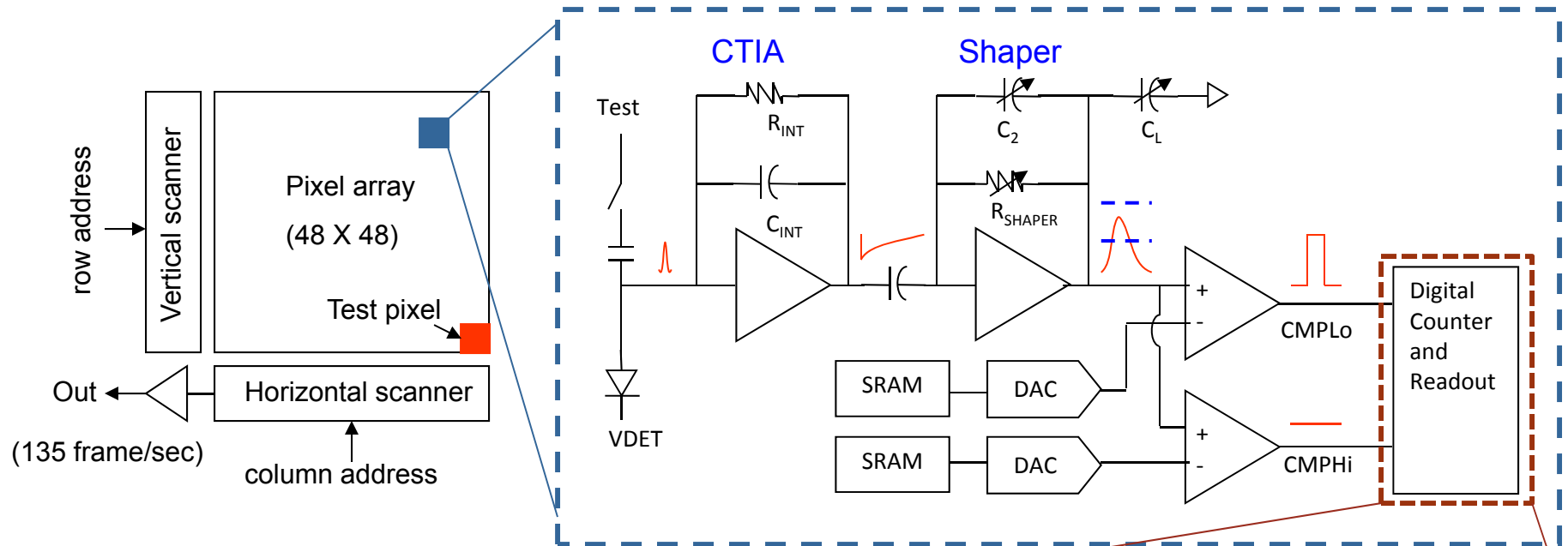
324-bunch mode: 50ps (FWHM) 11.4ns spacing



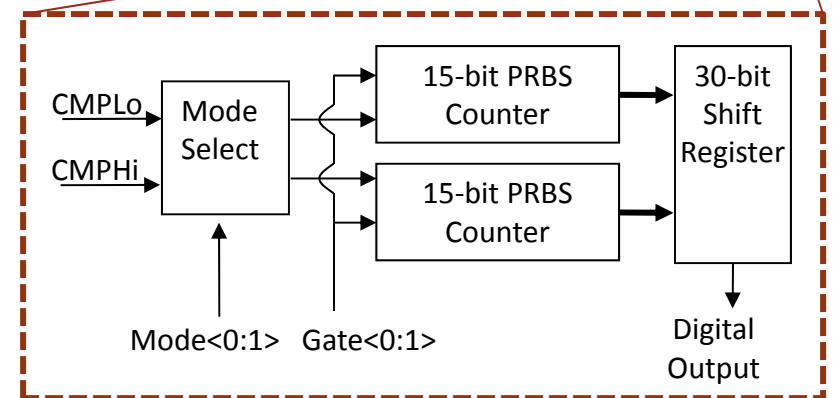
To utilize the full potential offered by APS

- Fast pulse pair resolution (10ns and 150 ns)
- Single photon counting (5k~20keV)
- Dual threshold counters (energy windowing)
- High dynamic range (1G counts/pixel)
- Gated counter operation (pump and probe)

DT-XPC Sensor Functionality

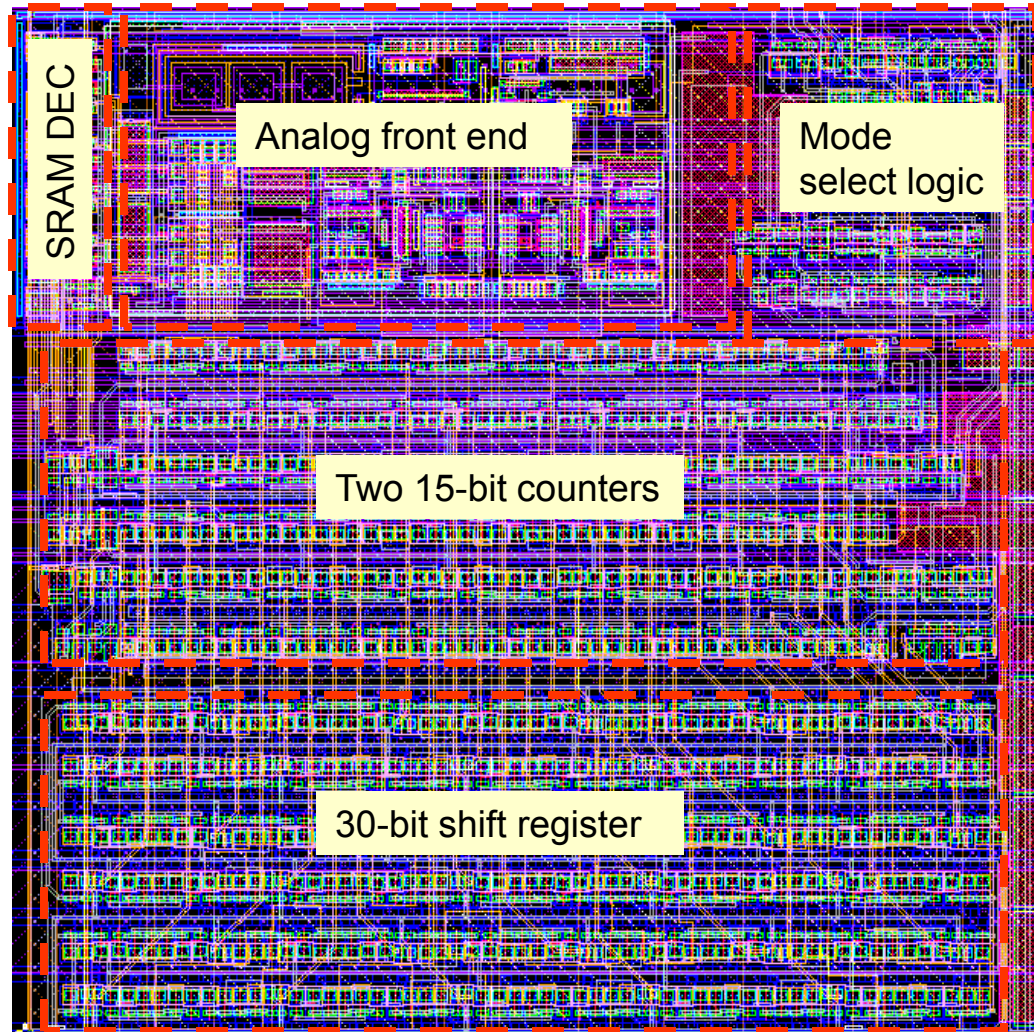


- By changing R_{shaper} , C_2 , and C_L , the width and amplitude of the shaper output pulse could be controlled and optimized for 10ns or 150ns bunch mode.
- With combination of comparator threshold, mode and gate signals, the device can support dual 15-bit counting, single 30 bit counting, energy windowing, and pump and probe testing.
- A 30-bit shift register allows the device to operate in integrate-while-read mode, resulting in minimum dead time of 3 μ s.



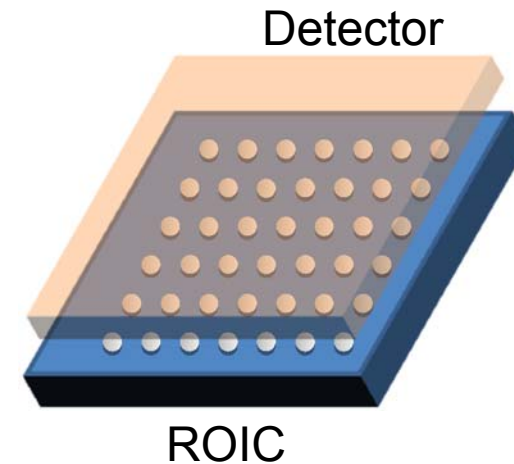
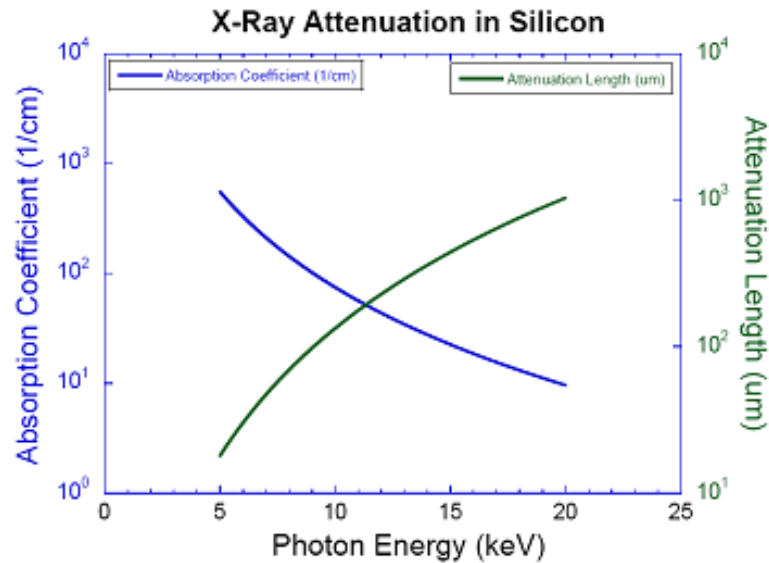
VOXTELOPTO

Pixel Layout



- TSMC 0.25 μm CMOS
- 130 μm by 130 μm
- 20% analog, 80% digital

Thick Silicon Detector Development



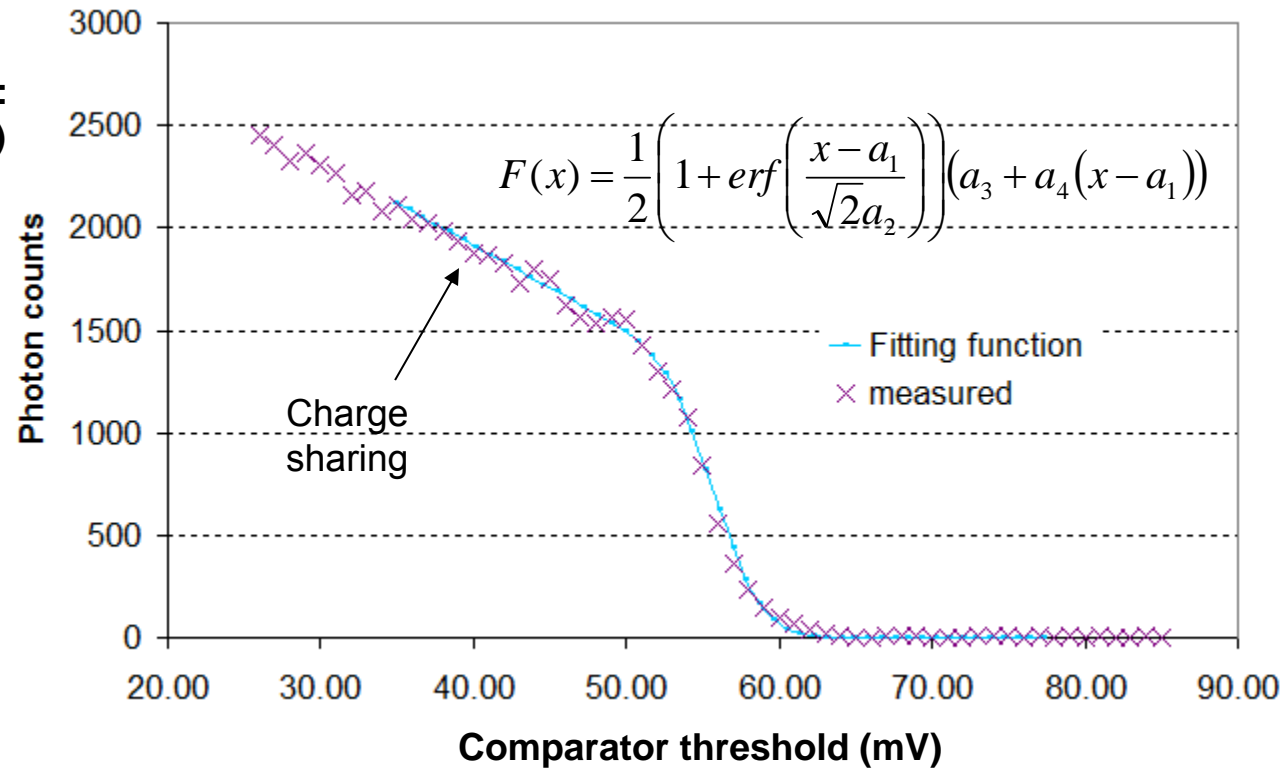
Working with the Advanced Photon Source at Argonne National Lab and Northern Illinois University, 520 μm thick, backside-illuminated silicon photodiode arrays were fabricated aiming for detection of X-rays in the range of 5keV to 20keV.

520 μm fully depleted silicon detector:

- Quantum efficiency: $\sim 90\%$ for 5keV and $\sim 40\%$ for 20keV X-rays.
- Response time: ~ 20 ns (too slow for 10 ns bunch mode)
- Germanium detector under development for 10 ns bunch mode**

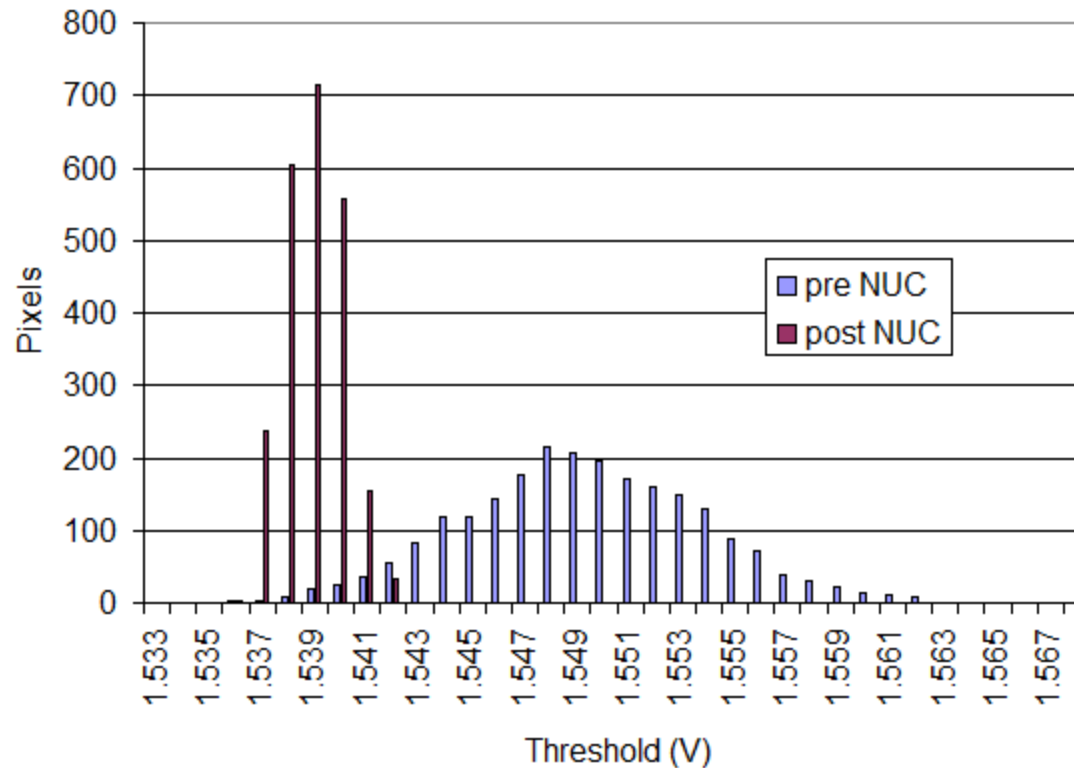
Threshold Scan with Iron-55

X-ray Source:
Fe55 (5.9keV)



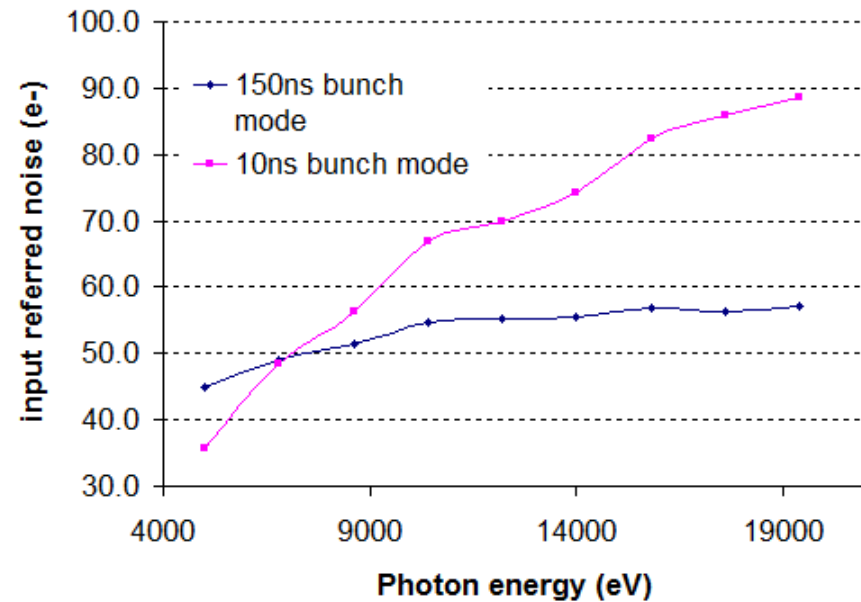
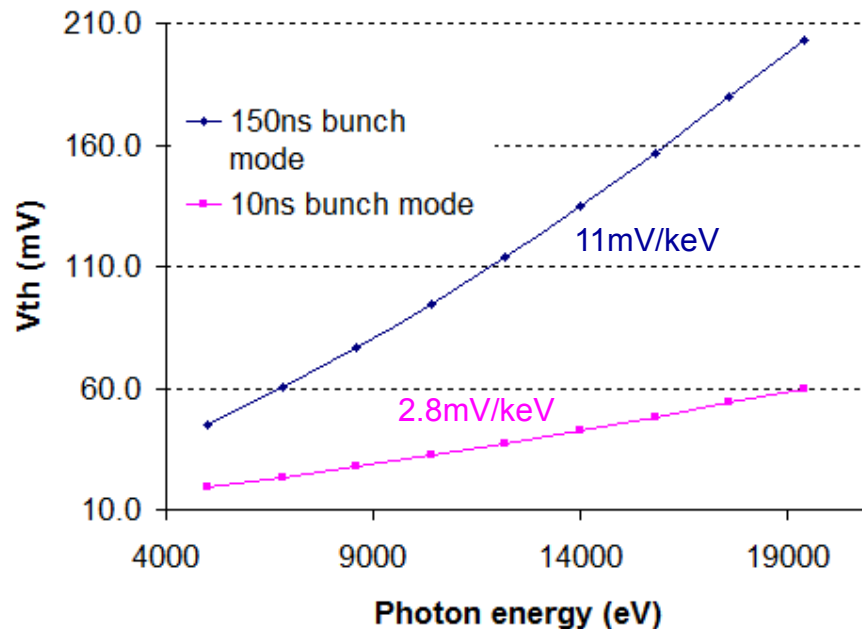
Conversion gain and noise numbers have been calculated from this threshold scan measurement. In 150ns bunch mode conversion gain is 32 $\mu\text{V}/e^-$ and the noise (detector + pixel circuitry + x-ray source) is 77.5 e^- or 283eV (RMS).

Non-Uniformity Correction



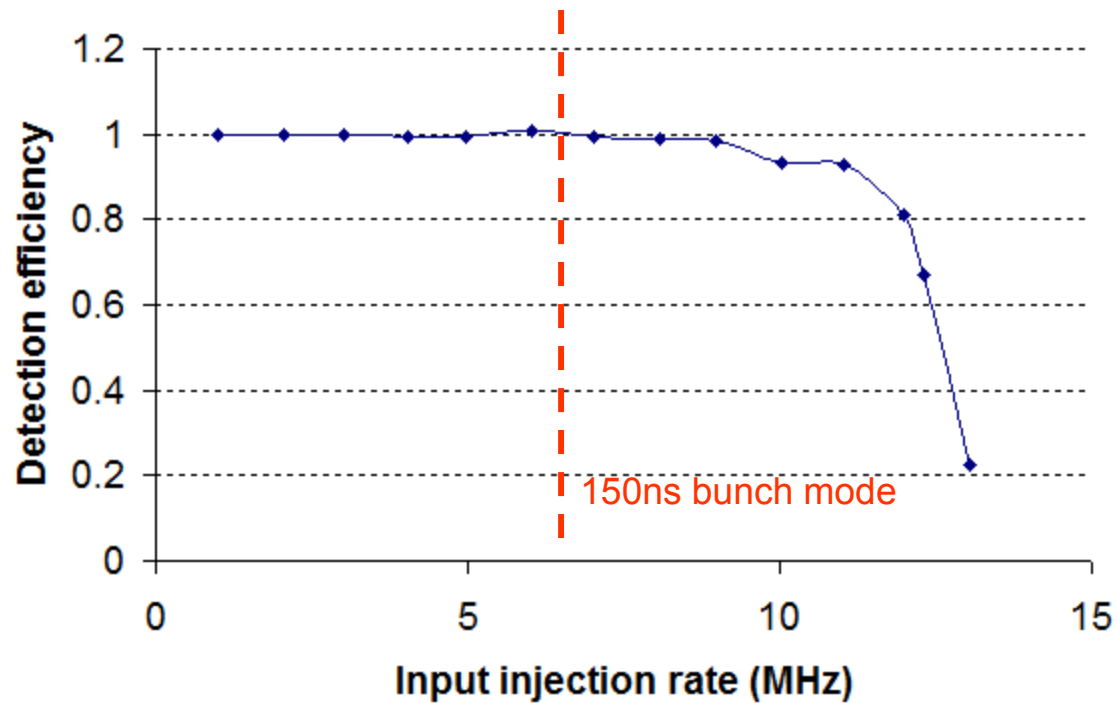
- Threshold distribution across the array when 5.9keV equivalent test charge is injected to each pixel.
- Distribution of threshold without NUC is 4.54 mV or 502 eV. Using the 3-bit in-pixel calibration of the comparator threshold, the non-uniformity is reduced to 1.15 mV or 127 eV.

Energy response



- Test pulse charge is injected to a pixel through in pixel charge injection circuitry
 - 150 ns bunch mode: charge pulse with 22 ns pulse width and 1 MHz repetition rate.
 - 10 ns bunch mode: charge pulse with 5 ns pulse width and 1 MHz repetition rate.
- 6.5% and 5.6% non-linearity on 150 ns and 10 ns bunch mode respectively across 5k~20keV.
- Input referred noise increases with photon energy especially for 10 ns bunch mode.

Detection Efficiency vs. Input Injection Rate



- 1060nm laser pulse with equivalent to 5.9 keV energy used for input source
- Almost no detection efficiency drop found up to 9 MHz

DT-XPC Sensor Summary and Future Developments

| Sensor Parameter | Units | Specification (150ns bunch mode) |
|------------------------------------|----------------------------|----------------------------------|
| Array size | pixels | 48 x 48 |
| Active area | mm | 6.24 x 6.24 |
| Pixel pitch | μm | 130 |
| X-ray energy | keV | 5 – 20 |
| Detector thickness (Si) | μm | 520 |
| Dynamic range | bits | 2 x 15 or 30 |
| Conversion gain | uV / e^- | 31 |
| Read noise (RMS) | e^- / eV | 46.7 / 170.5 |
| Threshold dispersion | e^- / eV | 34.8 / 127.2 |
| Minimum Bunch spacing (@ >1% loss) | ns | 110 |
| Power consumption | uW / pixel | 300 |

In Development

Beamline Camera

- DT-XPC sensor characterization testing is limited to Voxel's labs.
- **Planned:** Will move testing to Advanced Photon Source when beam-line camera is complete.

2nd Generation ROIC Design

- **Planned:** Will increase sensor active area to ~ 20 mm x 20 mm on reduced pixel pitch.

Germanium detector

- **Planned:** Will provide high stopping power and fast response time.



Thank you

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